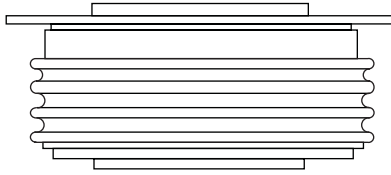


**Standard Recovery Diodes
(Hockey PUK Version), 1170 A**

DO-200AB (B-PUK)

FEATURES

- Wide current range
- High voltage ratings up to 3200 V
- High surge current capabilities
- Diffused junction
- Hockey PUK version
- Case style DO-200AB (B-PUK)
- Lead (Pb)-free
- Designed and qualified for industrial level

**RoHS**
COMPLIANT**PRODUCT SUMMARY**

$I_{F(AV)}$	1170 A
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TYPICAL APPLICATIONS

- Converters
- Power supplies
- Machine tool controls
- High power drives
- Medium traction applications

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	SD1100C..L		UNITS
		04 to 20	25 to 32	
$I_{F(AV)}$		1170	910	A
	T_{hs}	55	55	°C
$I_{F(RMS)}$		2080	1660	A
	T_{hs}	25	25	°C
I_{FSM}	50 Hz	13 000	10 500	A
	60 Hz	13 600	11 000	
I^2t	50 Hz	846	551	kA ² s
	60 Hz	772	503	
V_{RRM}	Range	400 to 2000	2500 to 3200	V
T_J		- 40 to 180	- 40 to 150	°C

SD1100C..L Series



Vishay High Power Products Standard Recovery Diodes
(Hockey PUK Version),
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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA
SD1100C..L	04	400	500	15
	08	800	900	
	12	1200	1300	
	16	1600	1700	
	20	2000	2100	
	25	2500	2600	
	30	3000	3100	
	32	3200	3300	

FORWARD CONDUCTION							
PARAMETER	SYMBOL	TEST CONDITIONS		SD1100C..L		UNITS	
				04 to 20	25 to 32		
Maximum average forward current at heatsink temperature	I _{F(AV)}	180° conduction, half sine wave Double side (single side) cooled		1170 (600)	910 (420)	A	
				55 (85)	55 (85)	°C	
Maximum RMS forward current	I _{F(RMS)}	25 °C heatsink temperature double side cooled		2080	1660		
Maximum peak, one-cycle forward, non-repetitive surge current	I _{FSM}	t = 10 ms	No voltage reappplied	Sinusoidal half wave, initial T _J = T _J maximum	13 000	10 500	A
		t = 8.3 ms			13 600	11 000	
		t = 10 ms	100 % V _{RRM} reappplied		10 930	8830	
		t = 8.3 ms			11 450	9250	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reappplied		846	551	kA ² s
		t = 8.3 ms			772	503	
		t = 10 ms	100 % V _{RRM} reappplied		598	390	
		t = 8.3 ms			546	356	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reappplied		8460	5510	kA ² √s	
Low level value of threshold voltage	V _{F(TO)1}	(16.7 % × π × I _{F(AV)} < I < π × I _{F(AV)}), T _J = T _J maximum		0.78	0.84	V	
High level value of threshold voltage	V _{F(TO)2}	(I > π × I _{F(AV)}), T _J = T _J maximum		0.94	0.88		
Low level value of forward slope resistance	r _{f1}	(16.7 % × π × I _{F(AV)} < I < π × I _{F(AV)}), T _J = T _J maximum		0.35	0.40	mΩ	
High level value of forward slope resistance	r _{f2}	(I > π × I _{F(AV)}), T _J = T _J maximum		0.26	0.38		
Maximum forward voltage drop	V _{FM}	I _{pk} = 1500 A, T _J = T _J maximum, t _p = 10 ms sinusoidal wave		1.31	1.44	V	



SD1100C..L Series

Standard Recovery Diodes Vishay High Power Products
(Hockey PUK Version), 1170 A

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	SD1100C..L		UNITS
			04 to 20	25 to 32	
Maximum junction operating temperature range	T_J		- 40 to 180	- 40 to 150	°C
Maximum storage temperature range	T_{Stg}		- 55 to 200		
Maximum thermal resistance, junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.11		K/W
		DC operation double side cooled	0.05		
Mounting force, $\pm 10\%$			9800 (1000)		N (kg)
Approximate weight			250		g
Case style		See dimensions - link at the end of datasheet	DO-200AB (B-PUK)		

ΔR_{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.011	0.011	0.008	0.008	$T_J = T_J$ maximum	K/W
120°	0.014	0.015	0.014	0.014		
90°	0.018	0.018	0.019	0.019		
60°	0.026	0.026	0.027	0.028		
30°	0.045	0.046	0.046	0.046		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

SD1100C..L Series



Vishay High Power Products Standard Recovery Diodes
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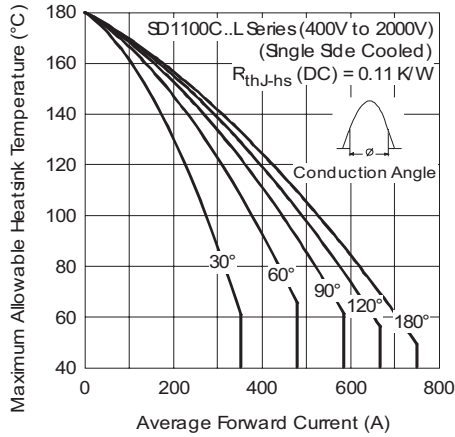


Fig. 1 - Current Ratings Characteristics

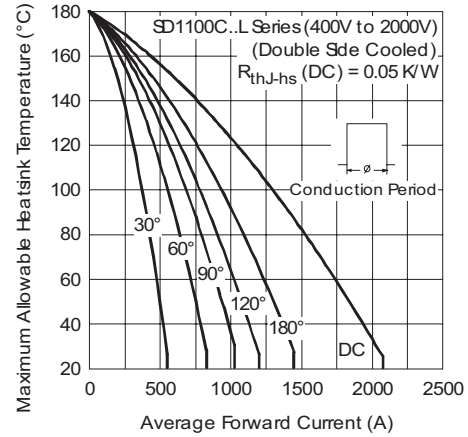


Fig. 4 - Current Ratings Characteristics

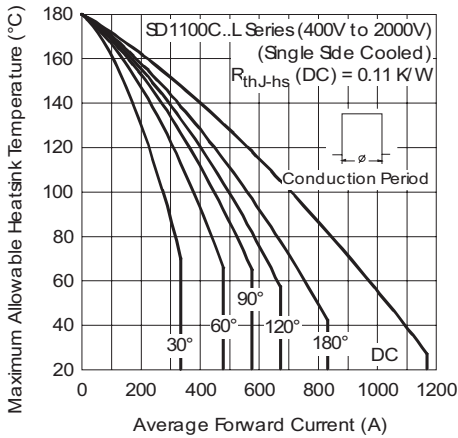


Fig. 2 - Current Ratings Characteristics

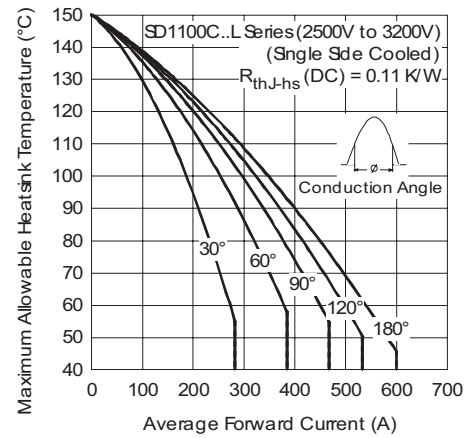


Fig. 5 - Current Ratings Characteristics

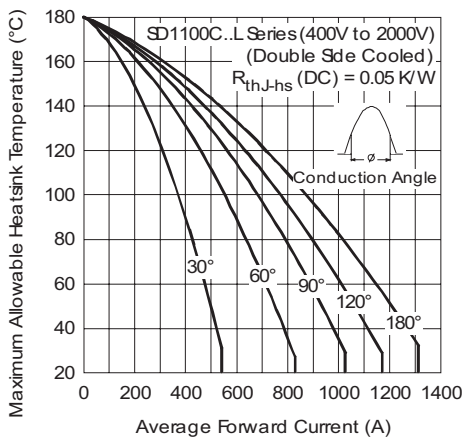


Fig. 3 - Current Ratings Characteristics

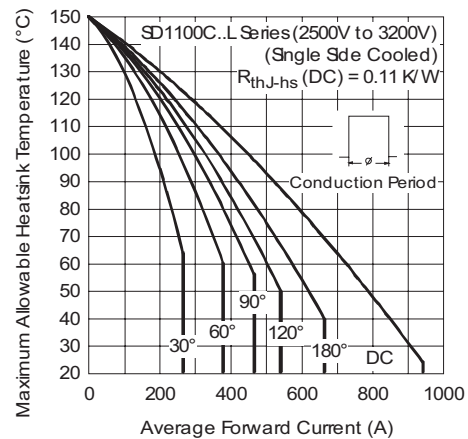


Fig. 6 - Current Ratings Characteristics



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Standard Recovery Diodes Vishay High Power Products
(Hockey PUK Version), 1170 A

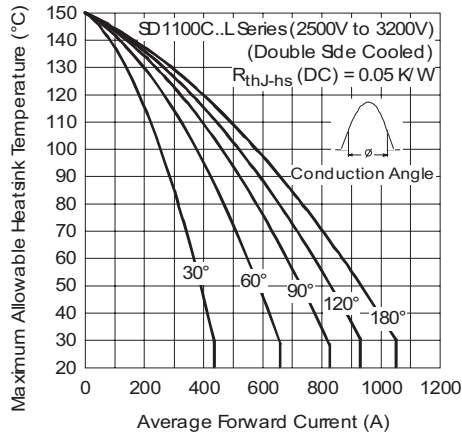


Fig. 7 - Current Ratings Characteristics

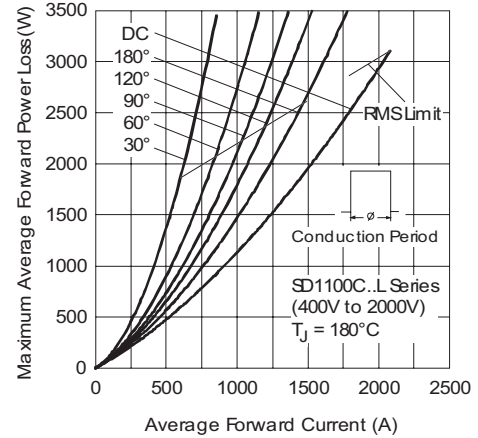


Fig. 10 - Forward Power Loss Characteristics

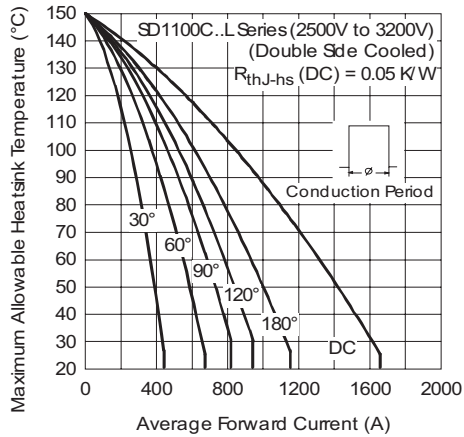


Fig. 8 - Current Ratings Characteristics

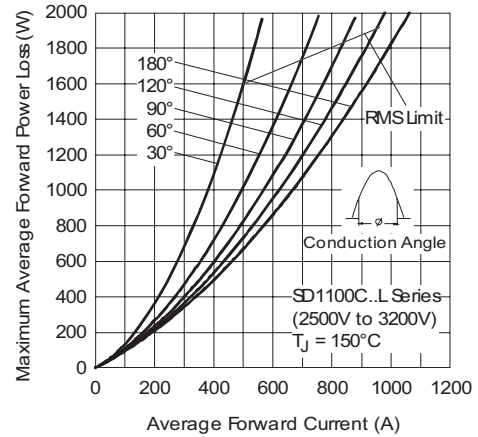


Fig. 11 - Forward Power Loss Characteristics

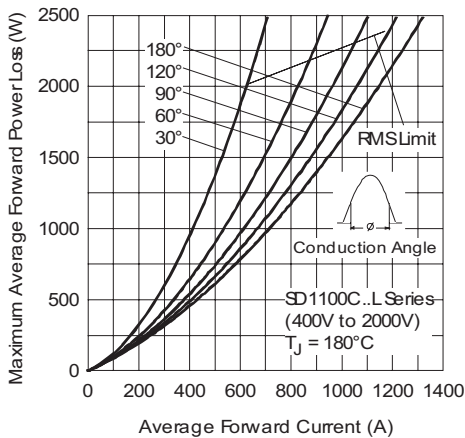


Fig. 9 - Forward Power Loss Characteristics

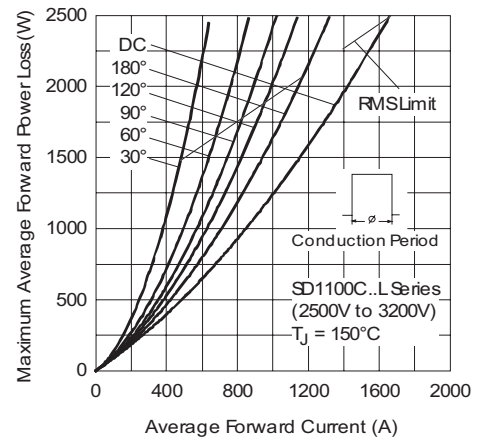


Fig. 12 - Forward Power Loss Characteristics

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Vishay High Power Products Standard Recovery Diodes (Hockey PUK Version), 1170 A

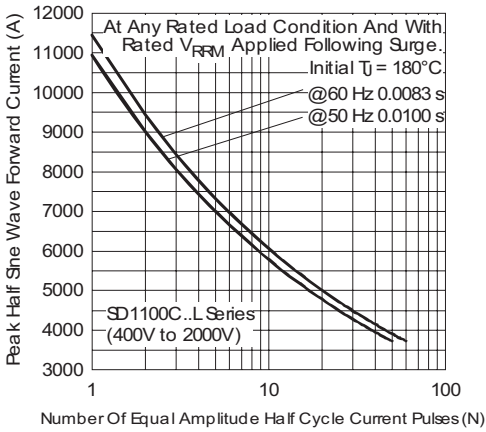


Fig. 13 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

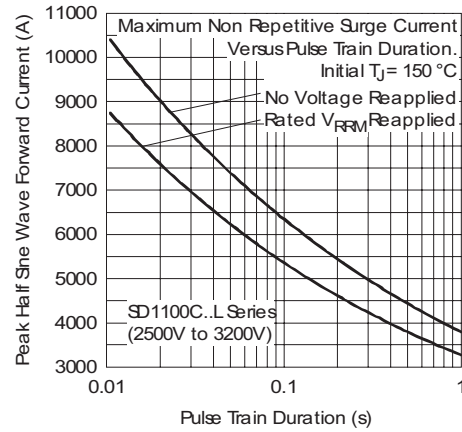


Fig. 16 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

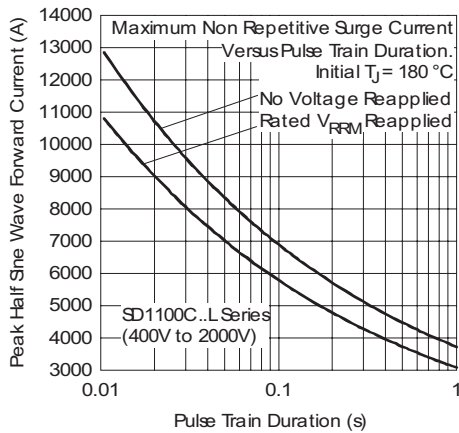


Fig. 14 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

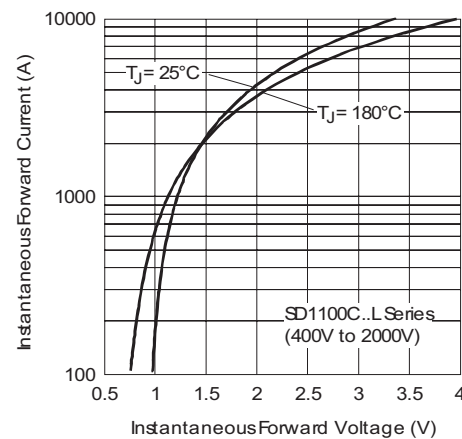


Fig. 17 - Forward Voltage Drop Characteristics

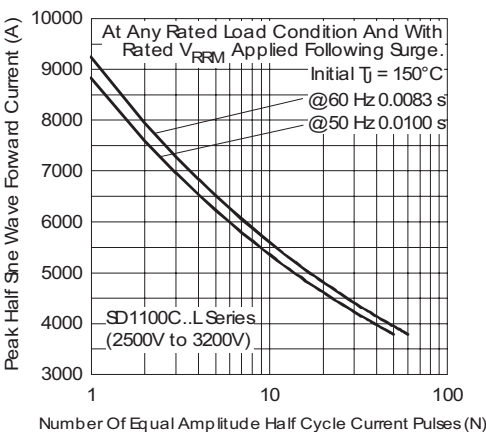


Fig. 15 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

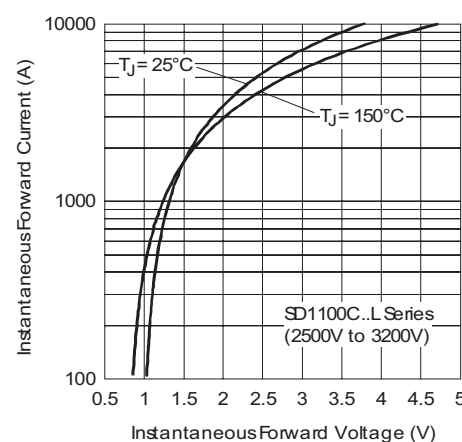


Fig. 18 - Forward Voltage Drop Characteristics



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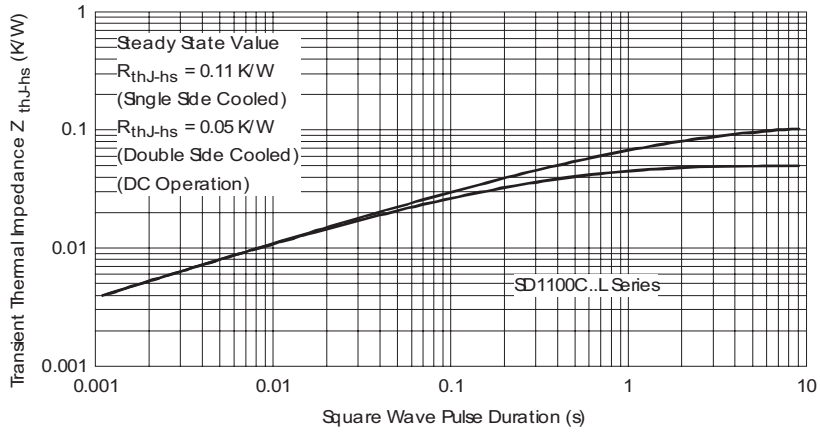
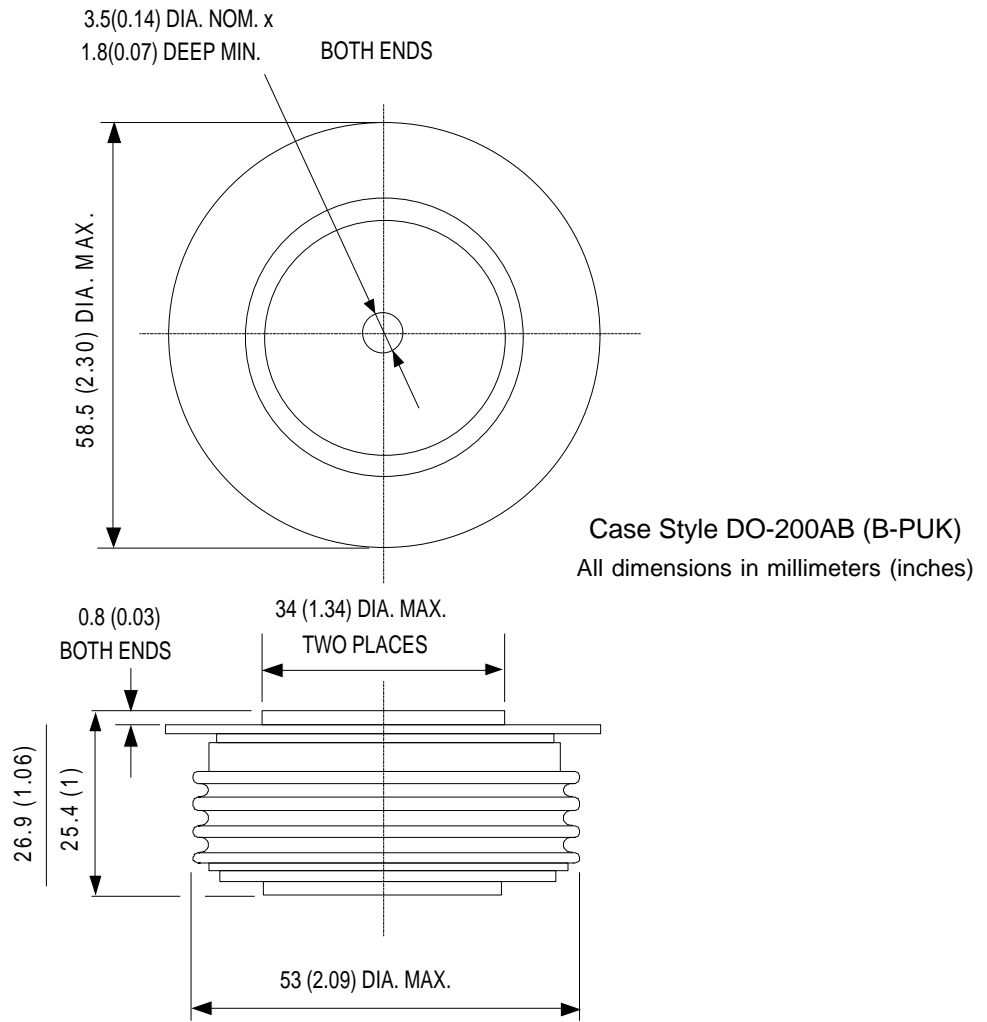


Fig. 19 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	SD	110	0	C	32	L
	①	②	③	④	⑤	⑥
	1	-	Diode			
	2	-	Essential part number			
	3	-	0 = Standard recovery			
	4	-	C = Ceramic PUK			
	5	-	Voltage code x 100 = V_{RRM} (see Voltage Ratings table)			
	6	-	L = PUK case DO-200AB (B-PUK)			

Outline Table





Notice

The products described herein were acquired by Vishay Intertechnology, Inc., as part of its acquisition of International Rectifier's Power Control Systems (PCS) business, which closed in April 2007. Specifications of the products displayed herein are pending review by Vishay and are subject to the terms and conditions shown below.

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